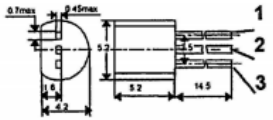
2N6027

Silicon programmable unijunction transistor (PUT's)
in package TO-92



Pinouts:
1- Cathode, 2- Gate, 3- Anode Part Marking: 6027

Ratings (T_A = 25°C)

Symbol	Parameter, units	Limits
V_{AK}	*Anode to cathode voltage, V	±40
V_{GKF}	*Gate to cathode forward voltage, V	40
V_{GKR}	*Gate to cathode reverse voltage, V	-5
V_{GAR}	*Gate to anode reverse voltage, V	40
I_T	*DC forward anode current, mA	150
I_{TRM}	Repetitive peak forward current, A 100µs Pulse width, 1% duty cycle *20µs Pulse width, 1% duty cycle	 1 2
P_T	*Power dissipation, mW	300

* - Anode positive, R_{GA} =1000Ω;
Anode negative, R_{GA}=open

Electrical Characteristics (T_A = 25°C)

Symbol	Parameter, units, test conditions	Limits		
		min	typ	max
I_P	Peak current, µA, V_S=10V, R_G=10kΩ		4	5
I_{GAO}	Gate to anode leakage current, nA, V_S=40V, cathode open		1	10
I_{GKS}	Gate to cathode leakage current, nA, V_S=40V, anode to cathode shorted		5	50
V_F	Forward voltage, V, I_F=50mA Peak		0.8	1.5
V_O	Peak output voltage, V, V_G=20V, C_C=0.2 µF	6	11	
V_T	Offset voltage, V V_S=10V, R_G=10kΩ	0.2	0.35	0.6
I_V	Valley current, µA, V_S=10V, R_G=10kΩ	70	150	
t_R	Pulse voltage rise time, ns V_B=20V, C_C =0.2 µF		40	80